ESD Protection Diode Array

Bi-directional ESD Protection for High-Speed Data Line

The NUP4000 surge protection is designed to protect equipment attached to up to four high speed communication lines from ESD, EFT, and lightning.

Features:

- SO-8 Package
- Peak Power 400 W 8 x 20 μS
- ESD Rating: IEC 61000-4-2 (ESD) ±15 kV (air) ±8 kV (contact) IEC 61000-4-4 (EFT) 40 A (5/50 ns) IEC 61000-4-5 (lightning) 12 A (8/20 μs)
- UL Flammability Rating of 94 V-0
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications:

- High Speed Communication Line Protection
- 15 V Data and I/O Lines
- Microprocessor Based Equipment
- LAN/WAN Equipment
- Servers
- Notebook and Desktop PC
- Serial and Parallel Ports
- Peripherals

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation 8 x 20 μ s @ T _A = 25°C (Note 1)	P _{pk}	400	W
Peak Pulse Current 8 x 20 μs @ T _A = 25°C (Note 1)	I _{PP}	10	A
Junction and Storage Temperature Range	T _J , T _{stg}	−55 to +150	°C
Lead Solder Temperature – Maximum 10 Seconds Duration	ΤL	260	°C

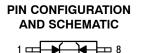
1. Non-repetitive current pulse 8 x 20 μ S exponential decay waveform

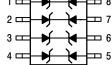


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SO-8 VOLTAGE SUPPRESSOR 400 WATTS PEAK POWER 15 VOLTS

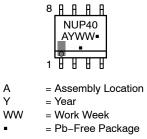






CASE 751

MARKING DIAGRAM



(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NUP4000DR2G	SO-8 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NUP4000

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	-	-	15	V
Reverse Breakdown Voltage @ I _t = 1.0 mA	V _{BR}	16.7	-	-	V
Reverse Leakage Current @ V _{RWM} = 15 Volts	I _R	N/A	-	1.0	μΑ
Maximum Clamping Voltage @ I_{PP} = 1.0 A, 8 x 20 μS	V _C	N/A	-	24	V
Maximum Clamping Voltage @ I_{PP} = 5.0 A, 8 x 20 μ S	V _C	N/A	-	30	V
Maximum Peak Pulse Current	I _{PP}	-	-	10	Α
Junction Capacitance @ V _R = 0 V, f = 1 MHz	CJ	-	-	75	pF

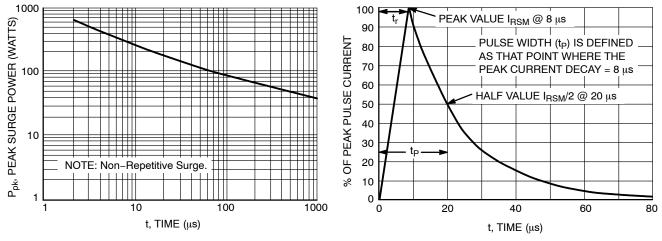


Figure 1. Pulse Width

Figure 2. 8 \times 20 μs Pulse Waveform

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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7.

8

COLLECTOR, #1

COLLECTOR, #1

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